



#4

In re Application of:  
Alton O. Christensen

Serial No.: 09/823,269

Confirmation No.: 7279

Filed: March 30, 2001

For: Improved Electroluminescent  
Devices and Displays with  
Integrally Fabricated Address  
and Logic Devices Fabricated by  
Printing or Weaving

Group Art Unit: 2879

Examiner: Unknown

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

CERTIFICATE OF MAILING 37 C.F.R. 1.8	
I hereby certify that this correspondence is being deposited on _____, 2001, with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231 on the date below:	
<u>9/24/01</u> Date	<u>William B. Patton</u> Signature

### PRELIMINARY AMENDMENT

Prior to examination, please amend the above-identified application as follows:

#### IN THE SPECIFICATION:

Please amend the specification by replacing paragraphs 19 and 21 with the following:

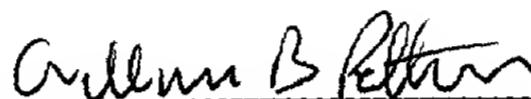
1. When contact is made between an n-type semiconductor and a conductor whose work function  $\Phi_m$  is less than half of  $(E_g/2 - \chi)$  where  $E_g$  is the semiconductor band gap and  $\chi$  is the electron affinity, then charge exchange occurs to obtain equilibrium;

3. the greater the positive difference between  $(E_g/2 + \chi - \Phi_m)$  and work function  $\Phi_m$  the greater charge exchange occurs to achieve equilibrium, filling some bulk traps as well; and."

#### REMARKS

The above amendments are made to correct some typographical errors in the specification. No new matter is added. Early and favorable action in connection with this application is respectfully requested.

Respectfully submitted,



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## APPENDIX

### IN THE SPECIFICATION:

1. When contact is made between an n-type semiconductor and a conductor whose work function  $\Phi_m$  is less than half of  $[(E_g/2 - \chi)]$   $(E_g/2 - \chi)$  where  $E_g$  is the semiconductor band gap and  $\chi$  is the electron affinity, then charge exchange occurs to obtain equilibrium;

3. the greater the positive difference between  $[(E_g/2 - \Phi_m)]$   $(E_g/2 + \chi - \Phi_m)$  and work function  $\Phi_m$  the greater charge exchange occurs to achieve equilibrium, filling some bulk traps as well; and.”.